# **Low Power Transistors**

## **PNP Silicon**

#### **Features**

- MIL-PRF-19500/357 Qualified
- Available as JAN, JANTX, JANTXV and JANHC

## **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	2N3634/L 2N3635/L	2N3636/L 2N3637/L	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	-140	-175	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-140 -175		Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	-5.0		Vdc
Collector Current - Continuous	I <sub>C</sub>	1.0		Adc
Total Device Dissipation @ T <sub>A</sub> = 25°C	P <sub>T</sub>	1.0		W
Total Device Dissipation @ T <sub>C</sub> = 25°C	P <sub>T</sub>	5.0		W
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200		°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	175	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	35	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

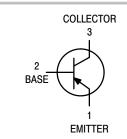
## **ORDERING INFORMATION**

Level	Device	Package	Shipping	
JAN JANTX JANTXV JANHC	2N3634			
	2N3635	TO-39	Bulk	
	2N3636	10–39		
	2N3637			
	2N3634L		D. die	
	2N3635L	TO-5		
	2N3636L	10–5	Bulk	
	2N3637L			



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TO-5 CASE 205AA STYLE 1 2N3634L 2N3635L 2N3636L 2N3637L

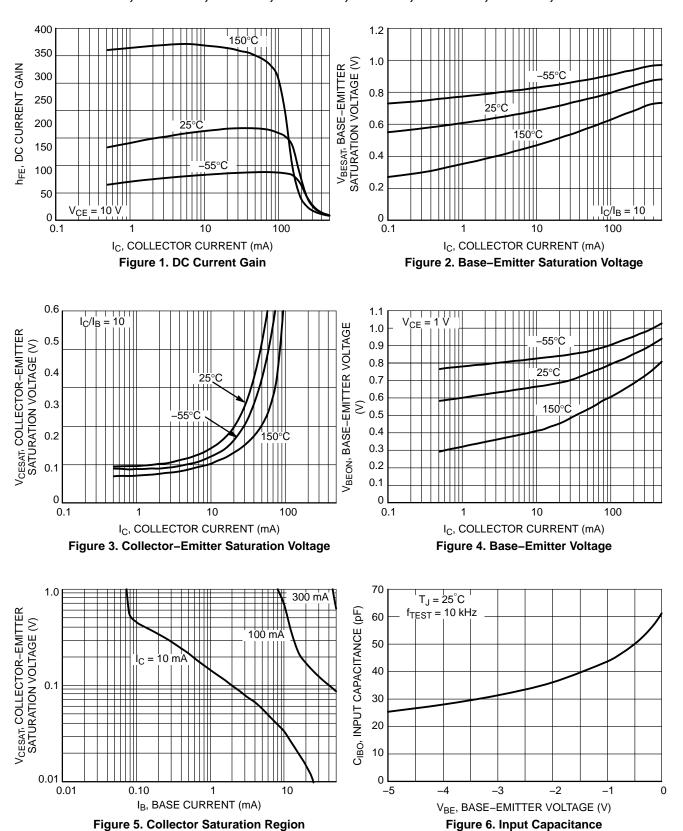


TO-39
CASE 205AB
STYLE 1
2N3634
2N3635
2N3636
2N3637

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS			•		
Collector – Emitter Breakdov (I <sub>C</sub> = –10 mA)	vn Voltage 2N3634, 2N3635 2N3636, 2N3637	V <sub>(BR)CEO</sub>	-140 -175	- -	V
Emitter-Base Cutoff Curren $(V_{EB} = -3.0 \text{ V})$ $(V_{EB} = -5.0 \text{ V})$	t	I <sub>EBO</sub>	<u>-</u>	-50 -10	nA μA
Collector–Emitter Cutoff Cut (V <sub>CE</sub> = -100 V)	rrent	I <sub>CEO</sub>	_	-10	μΑ
Collector–Base Cutoff Curre $(V_{CB} = -100 \text{ V})$ $(V_{CB} = -140 \text{ V})$ $(V_{CB} = -175 \text{ V})$	ent 2N3634, 2N3635 2N3636, 2N3637	Ісво	- - -	-100 -10 -10	nA μA μA
ON CHARACTERISTICS (N	Note 1)		···		I.
DC Current Gain $ \begin{aligned} &(I_C = -0.1 \text{ mA, } V_{CE} = -10 \\ &(I_C = -1.0 \text{ mA, } V_{CE} = -10 \\ &(I_C = -10 \text{ mA, } V_{CE} = -10 \\ &(I_C = -50 \text{ mA, } V_{CE} = -10 \\ &(I_C = -150 \text{ mA, } V_{CE} = -10 \\ \end{aligned} $	0 V) 0 V) 0 V)	h <sub>FE</sub>	25 45 50 50 30	- - - 150 -	-
DC Current Gain $ \begin{array}{l} (I_C = -0.1 \text{ mA, V}_{CE} = -10 \\ (I_C = -1.0 \text{ mA, V}_{CE} = -10 \\ (I_C = -10 \text{ mA, V}_{CE} = -10 \\ (I_C = -50 \text{ mA, V}_{CE} = -10 \\ (I_C = -150 \text{ mA, V}_{CE} = -10 \\ \end{array} $	0 V) 0 V) 0 V)	h <sub>FE</sub>	55 90 100 100 60	- - 300 -	-
Collector – Emitter Saturation ( $I_C = -10 \text{ mA}$ , $I_B = -1.0 \text{ r}$ ( $I_C = -50 \text{ mA}$ , $I_B = -5.0 \text{ r}$	mA)	V <sub>CE(sat)</sub>	- -	-0.3 -0.6	V
Base-Emitter Saturation Vo ( $I_C = -10 \text{ mA}, I_B = -1.0 \text{ r}$ ( $I_C = -50 \text{ mA}, I_B = -5.0 \text{ r}$	mA) ̃	V <sub>BE(sat)</sub>	_ -0.65	-0.8 -0.9	V
SMALL-SIGNAL CHARAC	TERISTICS		•		
Magnitude of Small–Signal (I <sub>C</sub> = -30 mA, V <sub>CE</sub> = -30		h <sub>fe</sub>	1.5 2.0	8.0 8.5	_
Small–Signal Current Gain ( $I_C = -10 \text{ mA}, V_{CE} = -10 \text{ mA}$ )	2N3634, 2N3636 2N3635, 2N3637	h <sub>fe</sub>	40 80	160 320	_
Output Capacitance (V <sub>CB</sub> = -20 V, I <sub>E</sub> = 0 A, 1	C <sub>obo</sub>	-	10	pF	
Input Capacitance $(V_{EB} = -1.0 \text{ V}, I_C = 0 \text{ A}, I_C = 0 \text{ A})$	C <sub>ibo</sub>	_	75	pF	
Noise Figure $(V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ r})$ $(V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ r})$ $(V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ r})$	NF	- - -	5.0 3.0 3.0	dB	
SWITCHING CHARACTER	ISTICS				
Delay Time	(Reference Figure 11 in MIL-PRF-19500/357)	t <sub>d</sub>	_	100	ns
Rise Time	(Reference Figure 11 in MIL-PRF-19500/357)	t <sub>r</sub>	_	100	ns
Storage Time	(Reference Figure 11 in MIL-PRF-19500/357)	t <sub>s</sub>	_	500	ns
Fall Time	(Reference Figure 11 in MIL-PRF-19500/357)	t <sub>f</sub>	_	150	ns
Turn-Off Time	(Reference Figure 11 in MIL-PRF-19500/357)	t <sub>off</sub>	-	600	ns

<sup>1.</sup> Pulse Test: Pulse Width = 300  $\mu s,$  Duty Cycle  $\leq$  2.0%.



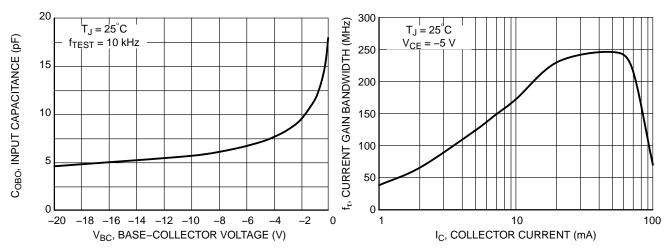
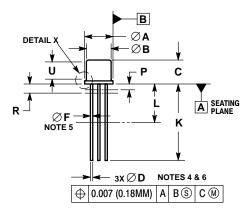


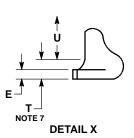
Figure 7. Output Capacitance

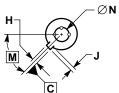
**Figure 8. Current Gain Bandwidth Product** 

### **PACKAGE DIMENSIONS**

TO-5 3-Lead CASE 205AA **ISSUE B** 









- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCHES.
- CONTROLLING DIMENSION: INCHES.
   CONTROLLING DIMENSION: INCHES.
   DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
   LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE PLANE DEFINED BY DIMENSION R.

- DIMENSION F APPLIES BETWEEN DIMENSION P AND L
  DIMENSION D APPLIES BETWEEN DIMENSION L AND K.
  BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMEN-SIONS A, B, AND T.
  DIMENSION B SHALL NOT VARY MORE THAN 0.010 IN ZONE P.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	8.89	9.40	0.350	0.370	
В	8.00	8.51	0.315	0.335	
С	6.10	6.60	0.240	0.260	
D	0.41	0.53	0.016	0.021	
Е	0.23	3.18	0.009	0.125	
F	0.41	0.48	0.016	0.019	
Н	0.71	0.86	0.028	0.034	
J	0.73	1.02	0.029	0.040	
K	38.10	44.45	1.500	1.750	
٦	6.35		0.250		
M	45°	45°BSC		45 °BSC	
N	5.08	BSC	0.200	BSC	
P		1.27		0.050	
R	1.37 BSC		0.054	BSC	
T		0.76		0.030	
U	2 54		0.100		

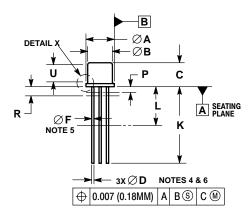
STYLE 1: PIN 1. EMITTER

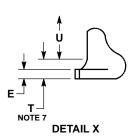
BASE

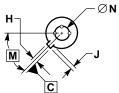
COLLECTOR

#### PACKAGE DIMENSIONS

## TO-39 3-Lead CASE 205AB **ISSUE A**









#### NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES.
- DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
- LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE PLANE DEFINED BY DIMENSION R.
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- BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMEN-SIONS A, B, AND T.
- DIMENSION B SHALL NOT VARY MORE THAN 0.010 IN ZONE P.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	8.89	9.40	0.350	0.370	
В	8.00	8.51	0.315	0.335	
С	6.10	6.60	0.240	0.260	
D	0.41	0.48	0.016	0.019	
E	0.23	3.18	0.009	0.125	
F	0.41	0.48	0.016	0.019	
H	0.71	0.86	0.028	0.034	
7	0.73	1.02	0.029	0.040	
K	12.70	14.73	0.500	0.580	
L	6.35		0.250		
M	45°BSC		45 °BSC		
N	5.08 BSC		0.200	0 BSC	
P		1.27		0.050	
R	1.37 BSC		0.054 BSC		
T		0.76		0.030	
U	2.54		0.100		

PIN 1. EMITTER

BASE

COLLECTOR

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